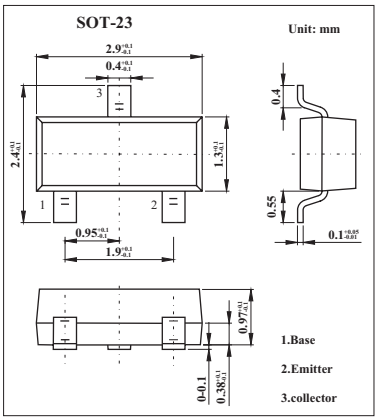
Small Signal Transistor

FMMT5087



■ Features

● Small signal transistor.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-50	V
Collector-emitter voltage	V_{CEO}	-50	V
Emitter-base voltage	V_{EBO}	-3	V
Collector current	I_C	-100	mA
Power dissipation	P_{tot}	330	mW
Operating and storage temperature range	T_j,T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	V_{CB}=-10V, I_E=0 V_{CB}=-35V, I_E=0			-10 -50	nA μA
Emitter cut-off current	I_{EBO}	V_{EB}=-3V, I_C=0			-50	nA
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-10mA, I_B=-1mA			-300	mV
Base-emitter on voltage	$V_{BE(on)}$	I_C=-1mA, V_{CE}=-5V			-850	mV
DC current gain	h_{FE}	I_C=-100mA, V_{CE}=-5V	250		800	
Current-gain-bandwidth product	f_T	I_C=-500mA, V_{CE}=-5V f=20MHz	40			MHz
Small signal current transfer	h_{fe}	I_C=-1mA, V_{CE}=-5V f=1KHz	250		900	
Noise figure	NF	I_C=200μA, V_{CE}=-5V, R_g=2KΩ f=30Hz to 15KHz at 2dB points			2	dB
Output capacitance	C_{obo}	V_{CB}=-5V, f=140MHz, I_E=0			4	pF

■ Marking

Marking	2m